

## 650V N-Channel Super Junction MOSFET

|                |              |              |               |
|----------------|--------------|--------------|---------------|
| <b>Voltage</b> | <b>650 V</b> | <b>Rdson</b> | <b>600 mΩ</b> |
| <b>Current</b> | <b>7.3 A</b> | <b>Qg</b>    | <b>17 nC</b>  |

### Feature:

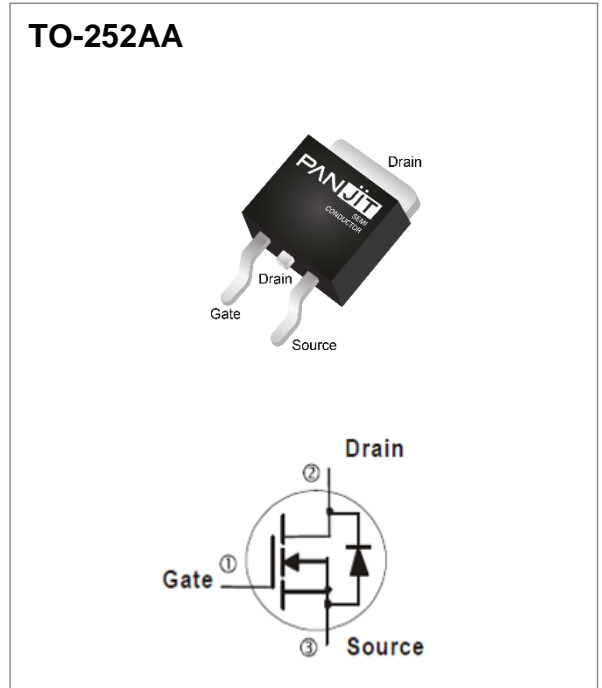
- $R_{DS(ON) Max, V_{GS}@10V}$ : 600mΩ
- Easy to use/ drive
- High Speed Switching and Low  $R_{DS(ON)}$
- 100% Avalanche Tested
- 100% Rg Tested
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

### Mechanical Data

- Case: TO-252AA package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0105 ounces, 0.297 grams

### Application

- PD Charger, Adapter, Monitor PSU



## Absolute Maximum Ratings ( $T_A = 25^\circ\text{C}$ unless otherwise specified)

| PARAMETER  |                         | SYMBOL         | LIMIT    | UNITS            |
|--|-------------------------|----------------|----------|------------------|
| Drain-Source Voltage @ $T_{jmax}$                |                         | $V_{DS}$       | 700      | V                |
| Drain-Source Voltage                             |                         | $V_{DS}$       | 650      |                  |
| Gate-Source Voltage                              |                         | $V_{GS}$       | $\pm 30$ |                  |
| Continuous Drain Current                         | $T_C=25^\circ\text{C}$  | $I_D$          | 7.3      | A                |
|  | $T_C=100^\circ\text{C}$ |                | 4.6      |                  |
| Pulsed Drain Current                             | $T_C=25^\circ\text{C}$  | $I_{DM}$       | 21.9     | A                |
| Single Pulse Avalanche Energy                    |                         | $E_{AS}$       | 78       | mJ               |
| MOSFET dv/dt ruggedness                          |                         | dv/dt          | 50       | V/ns             |
| Power Dissipation                                | $T_C=25^\circ\text{C}$  | $P_D$          | 54       | W                |
|  | $T_C=100^\circ\text{C}$ |                | 22       |                  |
| Operating Junction and Storage Temperature Range |                         | $T_J, T_{STG}$ | -55~150  | $^\circ\text{C}$ |

### Thermal Characteristics

| PARAMETER          |                              | SYMBOL          | MAXIMUM | UNITS              |
|--------------------|------------------------------|-----------------|---------|--------------------|
| Thermal Resistance | Junction-to-Case             | $R_{\theta JC}$ | 2.3     | $^\circ\text{C/W}$ |
|                    | Junction-to-Ambient (Note 3) | $R_{\theta JA}$ | 62.5    | $^\circ\text{C/W}$ |

**Electrical Characteristics** ( $T_A = 25\text{ }^\circ\text{C}$  unless otherwise specified)

| PARAMETER  | SYMBOL       | TEST CONDITION   | MIN. | TYP. | MAX.      | UNITS      |
|--|--------------|--|------|------|-----------|------------|
| <b>Static</b>  |              |  |      |      |           |            |
| Drain-Source Breakdown Voltage                           | $BV_{DSS}$   | $V_{GS}=0V, I_D=250\mu A$  | 650  | 730  | -         | V          |
| Gate Threshold Voltage                                   | $V_{GS(th)}$ | $V_{DS}=V_{GS}, I_D=250\mu A$                                      | 2    | 3.3  | 4         |            |
| Drain-Source On-State Resistance<br>(Note 1)             | $R_{DS(on)}$ | $V_{GS}=10V, I_D=2.1A$   | -    | 502  | 600       | m $\Omega$ |
| Zero Gate Voltage Drain Current                          | $I_{DSS}$    | $V_{DS}=650V, V_{GS}=0V$   | -    | -    | 1         | $\mu A$    |
| Gate-Source Leakage Current                              | $I_{GSS}$    | $V_{GS}=\pm 30V, V_{DS}=0V$  | -    | -    | $\pm 100$ | nA         |
| Transfer characteristics                                 | gfs          | $V_{DS}=20V, I_D=7.3A$   | -    | 7    | -         | S          |
| <b>Dynamic</b> (Note 5)                                  |              |  |      |      |           |            |
| Total Gate Charge  | $Q_g$        | $V_{DS}=520V, I_D=7.3A,$<br>$V_{GS}=10V$                           | -    | 17   | -         | nC         |
| Gate-Source Charge                                       | $Q_{gs}$     |  | -    | 4    | -         |            |
| Gate-Drain Charge  | $Q_{gd}$     |  | -    | 9    | -         |            |
| Input Capacitance  | $C_{iss}$    | $V_{DS}=400V, V_{GS}=0V,$<br>$f=250kHz$                            | -    | 554  | -         | pF         |
| Output Capacitance                                       | $C_{oss}$    |  | -    | 27   | -         |            |
| Reverse Transfer Capacitance                             | $C_{rss}$    |  | -    | 9    | -         |            |
| Effective Output Capacitance<br>Energy Related           | $C_{o(er)}$  | $V_{DS}=0V$ to 520V,<br>$V_{GS}=0V, f=250kHz$<br>(Note 4)          | -    | 33   | -         |            |
| Turn-On Delay Time                                       | $t_{d(on)}$  | $V_{DD}=325V, I_D=7.3A,$<br>$V_{GS}=10V, R_G=25\Omega$<br>(Note 2) | -    | 30   | -         |            |
| Turn-On Rise Time  | $t_r$        |  | -    | 44   | -         |            |
| Turn-Off Delay Time                                      | $t_{d(off)}$ |  | -    | 98   | -         |            |
| Turn-Off Fall Time                                       | $t_f$        |  | -    | 40   | -         |            |
| Gate Resistance  | $R_g$        | $f=1.0MHz$   | -    | 22   | -         | $\Omega$   |
| <b>Drain-Source Diode</b>                                |              |  |      |      |           |            |
| Maximum Continuous Drain-Source<br>Diode Forward Current | $I_S$        |  | -    | -    | 7.3       | A          |
| Diode Forward Voltage (Note 1)                           | $V_{SD}$     | $I_S=7.3A, V_{GS}=0V$  | -    | -    | 1.4       | V          |
| Reverse Recovery Charge                                  | $Q_{rr}$     | $I_S=7.3A$   | -    | 3.3  | -         | $\mu C$    |
| Reverse Recovery Time                                    | $T_{rr}$     | $di/dt=100A/\mu s$   | -    | 289  | -         | ns         |

NOTES :

1. Pulse width  $\leq 380\mu s$ , Duty cycle  $\leq 2\%$
2. Essentially independent of operating temperature typical characteristics.
3.  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance.
4.  $C_{o(er)}$  is a capacitance that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0V to 80%  $V_{(BR)DSS}$
5. Guaranteed by design, not subject to production testing

TYPICAL CHARACTERISTIC CURVES

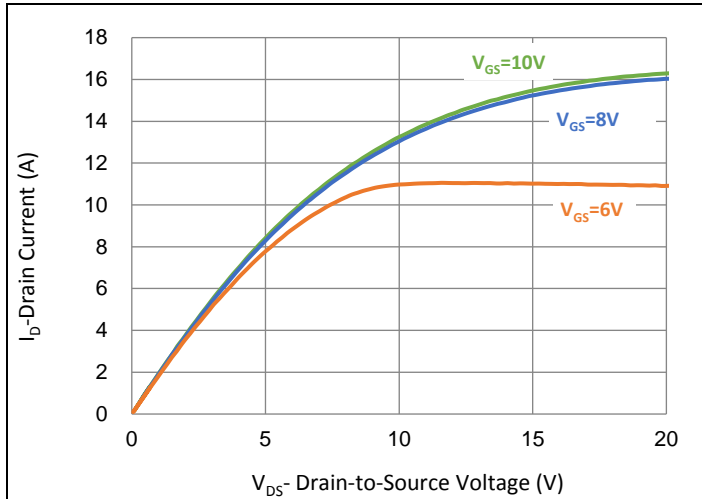


Fig.1 Output Characteristics

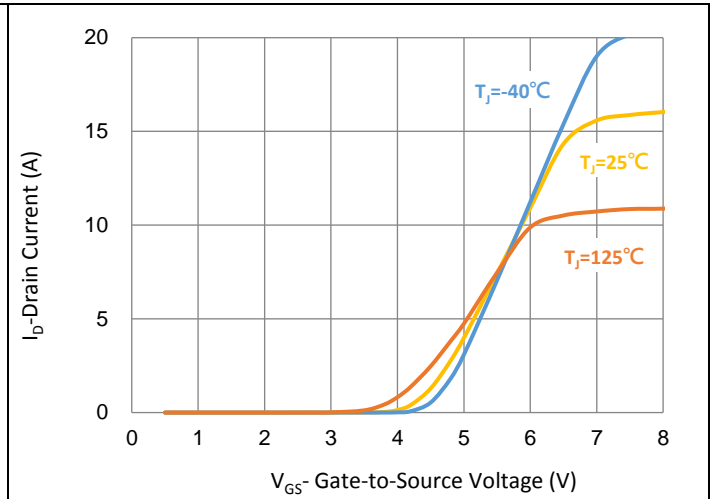


Fig.2 Transfer Characteristics

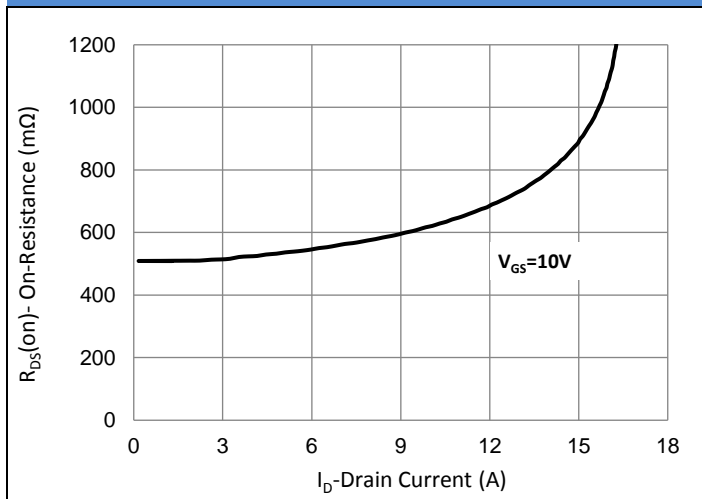


Fig.3 On-Resistance vs. Drain Current

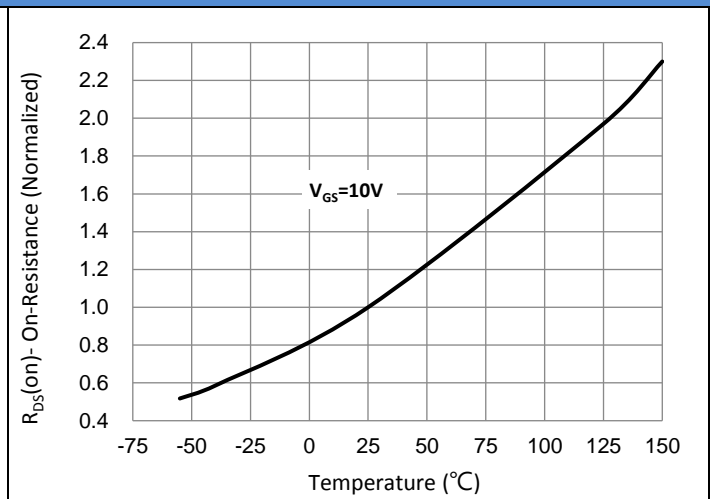


Fig.4 On-Resistance vs. Junction Temperature

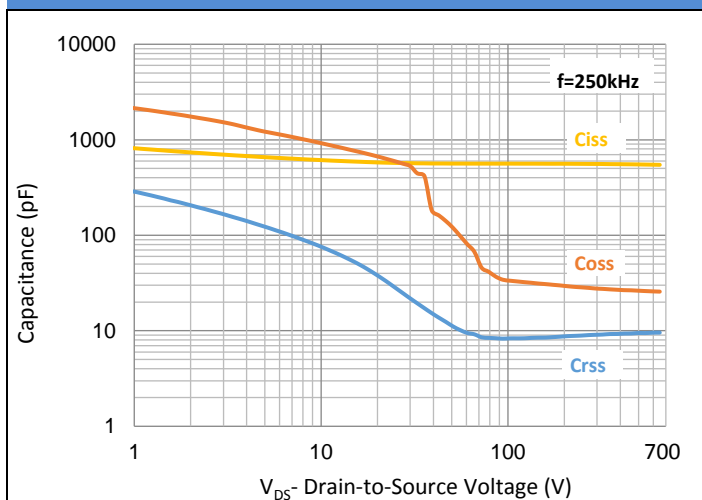


Fig.5 Capacitance vs. Drain-Source Voltage

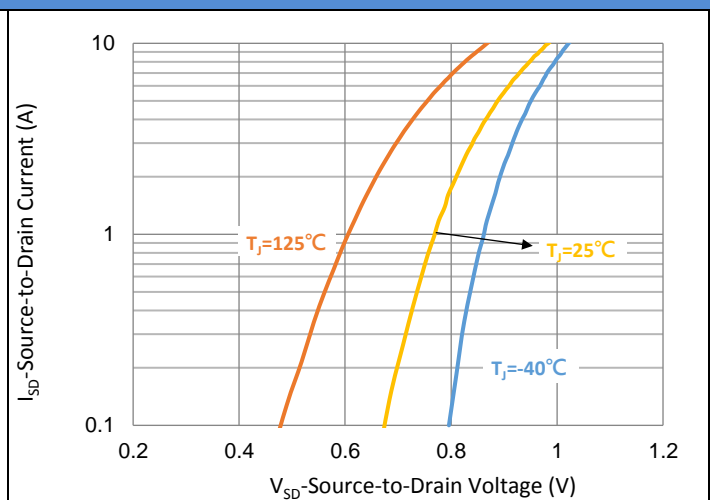
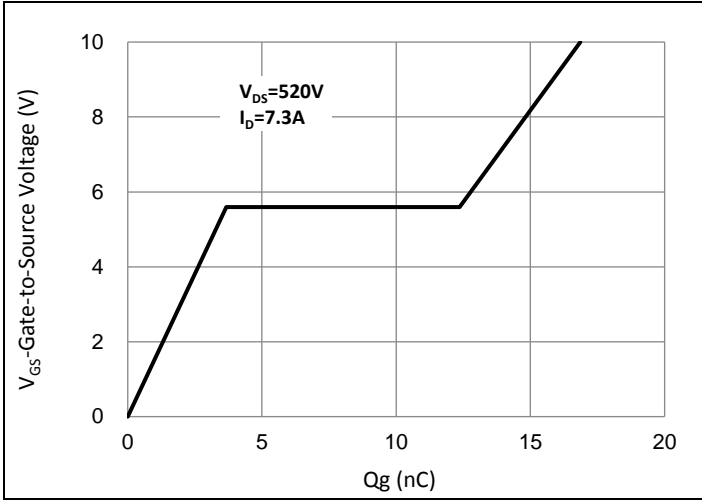
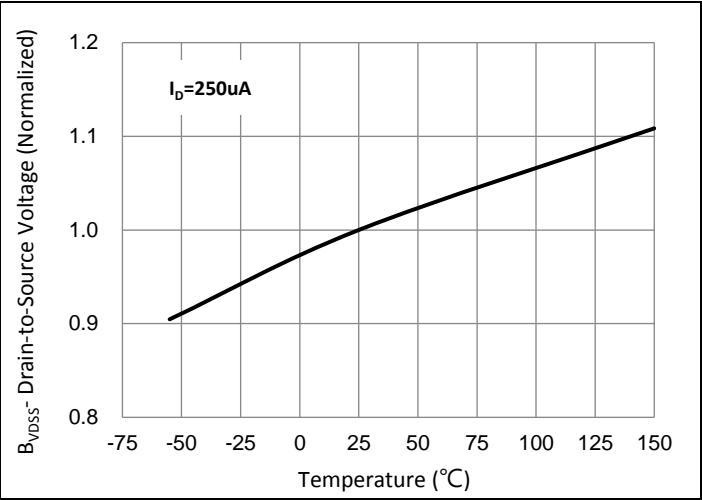


Fig.6 Source-Drain Diode Forward Voltage

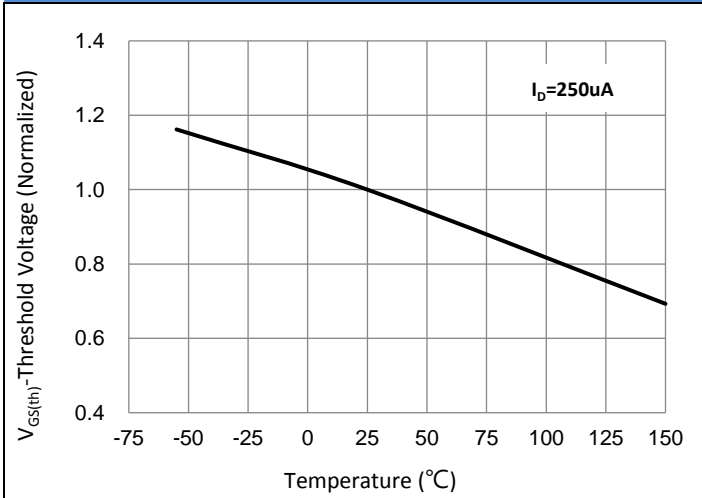
**TYPICAL CHARACTERISTIC CURVES**



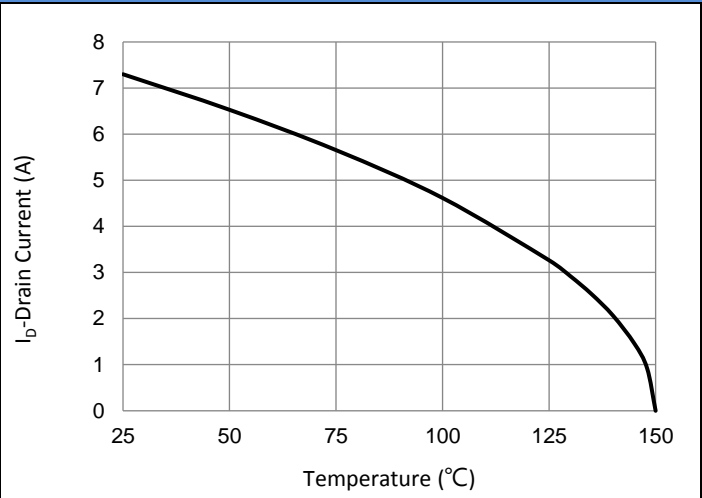
**Fig.7 Gate-Charge Characteristics**



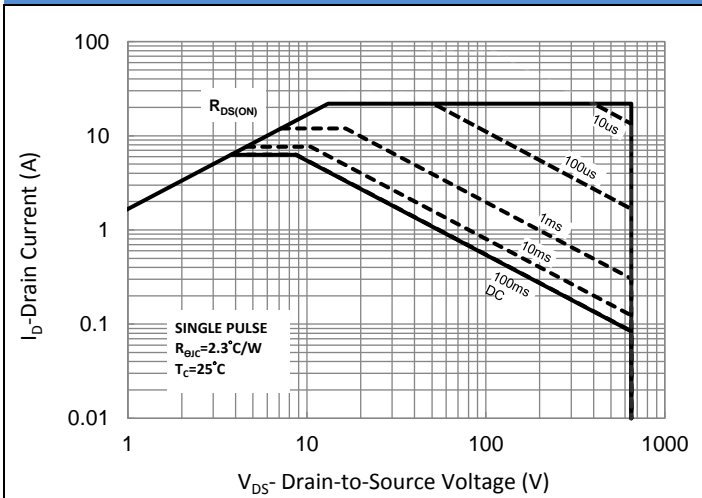
**Fig.8 Breakdown Voltage Variation vs. Temperature**



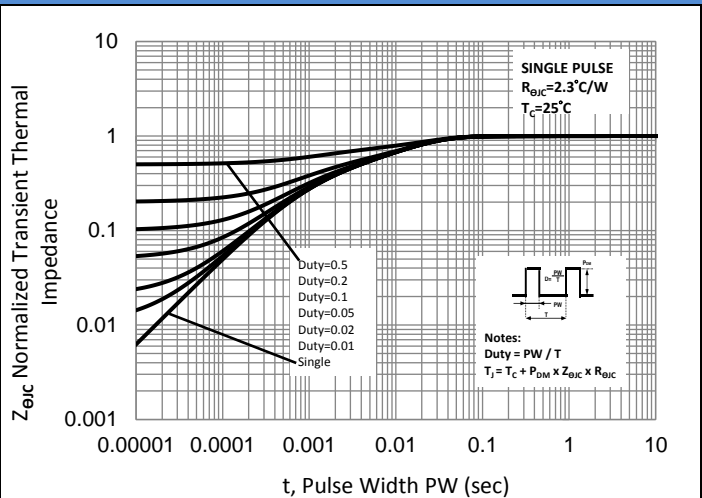
**Fig.9 Threshold Voltage Variation with Temperature**



**Fig.10 Drain Current vs. Case Temperature**



**Fig.11 Maximum Safe Operating Area**



**Fig.12 Normalized Transient Thermal Impedance**

TYPICAL CHARACTERISTIC CURVES

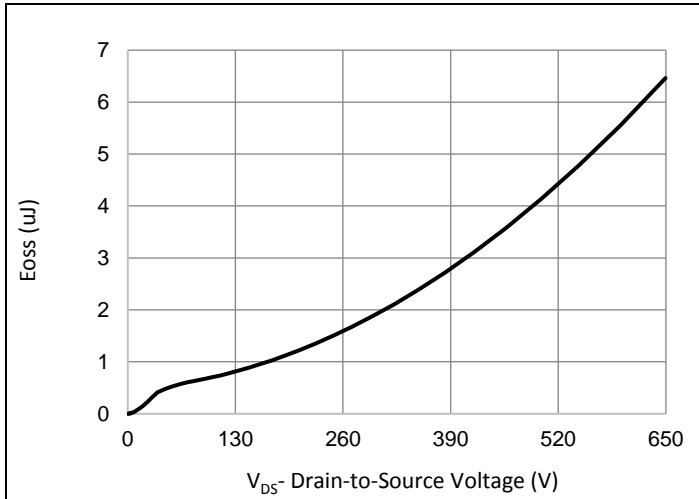
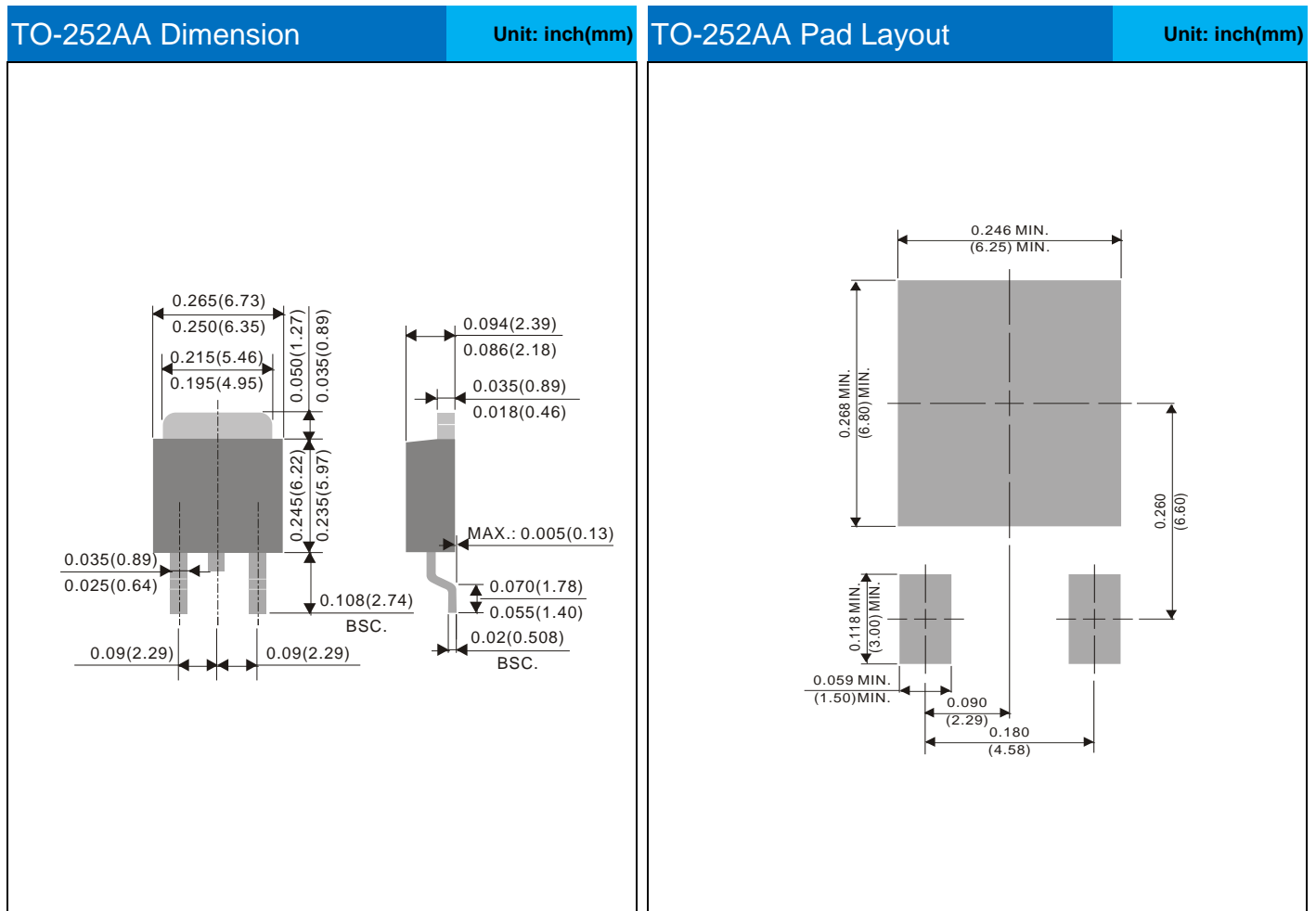


Fig.13 Typ. Coss Stored Energy

**Product and Packing Information**

| Part No.     | Package Type | Packing Type        | Marking  |
|--------------|--------------|---------------------|----------|
| PJMD600N65E1 | TO-252AA     | 3,000pcs / 13" reel | 600N65E1 |

**Packaging Information**



**Marking Diagram**

|                          |   |
|--------------------------|---|
| PJ<br>600N65E1<br>YWLL x | <b>Y</b> = Year Code<br><b>W</b> = Week Code (A~Z)<br><b>LL</b> = Lot Code (00~99)<br><b>x</b> = Production Line Code |
|--------------------------|---|

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